

Mohsen Nami

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Carrier Dynamics and Electro-Optical Characterization of High-Performance GaN/InGaN Core-Shell Nanowire Light-Emitting Diodes. Scientific Reports, 2018, 8, 501.	1.6	69
2	High-Speed Nonpolar InGaN/GaN LEDs for Visible-Light Communication. IEEE Photonics Technology Letters, 2017, 29, 381-384.	1.3	67
3	Electrically Injected GHz-Class GaN/InGaN Core-Shell Nanowire-Based LEDs: Carrier Dynamics and Nanoscale Homogeneity. ACS Photonics, 2019, 6, 1618-1625.	3.2	52
4	Differential carrier lifetime and transport effects in electrically injected III-nitride light-emitting diodes. Journal of Applied Physics, 2017, 122, .	1.1	47
5	Tunable microwave signal generator with an optically-injected 1310nm QD-DFB laser. Optics Express, 2013, 21, 10772.	1.7	43
6	Scalable Top-Down Approach Tailored by Interferometric Lithography to Achieve Large-Area Single-Mode GaN Nanowire Laser Arrays on Sapphire Substrate. ACS Nano, 2018, 12, 2373-2380.	7.3	41
7	Explanation of low efficiency droop in semipolar (202Å ⁻¹ Å ⁻¹) InGaN/GaN LEDs through evaluation of carrier recombination coefficients. Optics Express, 2017, 25, 19343.	1.7	34
8	Nanoporous distributed Bragg reflectors on free-standing nonpolar c-plane GaN. Applied Physics Letters, 2018, 112, .	1.5	34
9	Tailoring the morphology and luminescence of GaN/InGaN core-shell nanowires using bottom-up selective-area epitaxy. Nanotechnology, 2017, 28, 025202.	1.3	30
10	Internal quantum efficiency and carrier dynamics in semipolar (20Tj ETQq0 0 0 rgBT/Overlock 10 Tf 50</i> InGaN/GaN LEDs. Applied Physics Letters, 2017, 111, 172101.	1.7	29
11	Trade-off between bandwidth and efficiency in semipolar (202Å ⁻¹ Å ⁻¹) InGaN/GaN single- and multiple-quantum-well light-emitting diodes. Applied Physics Letters, 2018, 112, .	1.5	27
12	Optical properties of plasmonic light-emitting diodes based on flip-chip III-nitride core-shell nanowires. Optics Express, 2014, 22, 29445.	1.7	25
13	GaN nanowire tips for nanoscale atomic force microscopy. Nanotechnology, 2017, 28, 20LT01.	1.3	18
14	Bistability patterns and nonlinear switching with very high contrast ratio in a 1550nm quantum dash semiconductor laser. Applied Physics Letters, 2012, 101, .	1.5	17
15	Semipolar InGaN/GaN nanostructure light-emitting diodes on c-plane sapphire. Applied Physics Express, 2016, 9, 032101.	1.1	17
16	Optical properties of Ag-coated GaN/InGaN axial and core-shell nanowire light-emitting diodes. Journal of Optics (United Kingdom), 2015, 17, 025004.	1.0	14
17	Reduction of reverse leakage current in selective-area-grown GaN-based core-shell nanostructure LEDs using AlGaIn layers. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600776.	0.8	14
18	In situ and selective area etching of GaN by tertiarybutylchloride (TBCl). Applied Physics Letters, 2019, 115, .	1.5	9

#	ARTICLE	IF	CITATIONS
19	A study of damage-free in-situ etching of GaN in metalorganic chemical vapor deposition (MOCVD) by tertiarybutylchloride (TBCl). Journal of Crystal Growth, 2020, 534, 125492.	0.7	9
20	Rapid Screen for Antiviral Tâ€Cell Immunity with Nanowire Electrochemical Biosensors. Advanced Materials, 2022, 34, e2109661.	11.1	9
21	Selective Area Regrowth Produces Nonuniform Mg Doping Profiles in Nonplanar GaN pâ€n Junctions. ACS Applied Electronic Materials, 2021, 3, 704-710.	2.0	8
22	Two-Wavelength Switching With a 1310-nm Quantum Dot Distributed Feedback Laser. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1900708-1900708.	1.9	7
23	Ordered arrays of bottom-up III-nitride core-shell nanostructures. , 2015, , .		6
24	Analysis of light extraction efficiency for gallium nitride-based coaxial microwall light-emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 766-770.	0.8	5
25	Spectrally-resolved internal quantum efficiency and carrier dynamics of semipolar \$(10\bar{a}r\{1\}1)\$ core-shell triangular nanostripe GaN/InGaN LEDs. Nanotechnology, 2018, 29, 235206.	1.3	5
26	Etched-And-Regrown GaN Pâ€N Diodes with Low-Defect Interfaces Prepared by In Situ TBCl Etching. ACS Applied Materials & Interfaces, 2021, 13, 53220-53226.	4.0	3
27	Designing Sensitivity: A Comparative Analysis of Microelectrode Topologies for Electrochemical Oxygen Sensing in Biomedical Applications. Micromachines, 2022, 13, 141.	1.4	2
28	Investigation of Purcell Factor and Light Extraction Efficiency in Ag-Coated GaN/InGaN Core-Shell Nanowires. , 2014, , .		1
29	CMOS-compatible silicon nanowire field-effect transistors: Where nanotechnology pushes the limits in biosensing. , 2022, , 327-362.		1
30	Improving micromachining: process using a new mode converter system. , 0, , .		0
31	Bistability and switching with very high contrast ratio in an optically-injected 1550nm-QDash Fabry-Perot laser. , 2012, , .		0
32	Analysis and applications of an optically-injected 1310 nm Quantum-Dot Distributed Feedback laser. , 2013, , .		0
33	Tunable microwave, millimeter-wave and THz signal generation with a 1310nm quantum dot laser. , 2013, , .		0
34	Two-wavelength switching with a 1310nm-QDot DFB laser. , 2013, , .		0
35	Investigation of plasmonic enhancement in a quantum dot-in-a-well structure. Proceedings of SPIE, 2015, , .	0.8	0
36	High-Speed Nonpolar InGaN/GaN LEDs for Visible-Light Communication. , 2017, , .		0

#	ARTICLE	IF	CITATIONS
37	Laser Interferometry for Precise Measurement of Ultralow Flow Rates from Permeable Materials. Environmental Science and Technology Letters, 2022, 9, 233-238.	3.9	0